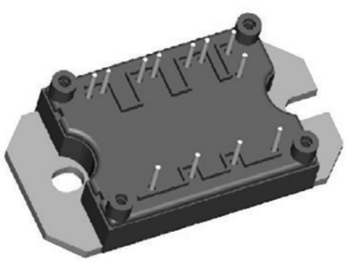
"Half Bridge" MTP Trench IGBT, 75 A



MTP

FEATURES

- Trench gate field stop technology
- Positive $V_{CE(on)}$ temperature coefficient
- 5 μs short circuit capability
- Square RBSOA
- HEXFRED® antiparallel diodes with ultrasoft reverse recovery and low V_F
- Al_2O_3 DBC
- Very low stray inductance design for high speed operation
- UL approved file E78996
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Pb-free Available
RoHS* Available

Note
* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

PRIMARY CHARACTERISTICS	
V_{CES}	1200 V
$V_{CE(on)}$ typical at I_C = 40 A	2.24 V
I_C at T_C = 25 °C	75 A
Speed	8 kHz to 30 kHz
Package	MTP
Circuit configuration	Half bridge

BENEFITS

- Optimized for welding, UPS and SMPS applications
- Rugged with ultrafast performance
- Benchmark efficiency above 20 kHz
- Outstanding ZVS and hard switching operation
- Low EMI, requires less snubbing
- Excellent current sharing in parallel operation
- Direct mounting to heatsink
- PCB solderable terminals
- Very low junction to case thermal resistance

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter breakdown voltage	V_{CES}		1200	V
Continuous collector current	I_C	T_C = 25 °C	75	A
		T_C = 102 °C	40	
Pulsed collector current	I_{CM}	T_J = 150 °C, t_p = 6 ms, V_{GE} = 15 V	150	
Clamped inductive load current	I_{LM}		120	
Diode continuous forward current	I_F	T_C = 105 °C	21	
Diode maximum forward current	I_{FM}		160	
Gate to emitter voltage	V_{GE}		± 20	V
RMS isolation voltage	V_{ISOL}	Any terminal to case, t = 1 min	2500	
Maximum power dissipation (only IGBT)	P_D	T_C = 25 °C	305	W
		T_C = 100 °C	122	

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Collector to emitter breakdown voltage	$V_{(BR)CES}$	V_{GE} = 0 V, I_C = 2 mA	1200	-	-	V
Collector to emitter saturation voltage	$V_{CE(on)}$	V_{GE} = 15 V, I_C = 40 A	-	2.24	2.65	V
		V_{GE} = 15 V, I_C = 80 A	-	2.84	-	
		V_{GE} = 15 V, I_C = 40 A, T_J = 150 °C	-	2.53	-	
		V_{GE} = 15 V, I_C = 80 A, T_J = 150 °C	-	3.44	-	
Gate threshold voltage	$V_{GE(th)}$	V_{CE} = V_{GE}, I_C = 2 mA	4.6	5.9	7.6	
Temperature coefficient of threshold voltage	$V_{GE(th)}/\Delta T_J$	V_{CE} = V_{GE}, I_C = 2 mA (25 °C to 125 °C)	-	-13	-	mV/°C
Transconductance	g_{fe}	V_{CE} = 50 V, I_C = 40 A	-	29	-	S
Zero gate voltage collector current	I_{CES}	V_{GE} = 0 V, V_{CE} = 1200 V, T_J = 25 °C	-	0.6	50	µA
		V_{GE} = 0 V, V_{CE} = 1200 V, T_J = 125 °C	-	0.31	-	mA
		V_{GE} = 0 V, V_{CE} = 1200 V, T_J = 150 °C	-	1.16	-	
Gate to emitter leakage current	I_{GES}	V_{GE} = ± 20 V	-	-	±250	nA

SWITCHING CHARACTERISTICS (T_J = 25 °C unless otherwise specified)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Total gate charge (turn-on)	Q_g	I_C = 40 A V_{CC} = 960 V V_{GE} = 15 V	-	158	-	nC
Gate to emitter charge (turn-on)	Q_{ge}		-	17	-	
Gate to collector charge (turn-on)	Q_{gc}		-	85	-	
Turn-on switching loss	E_{on}	V_{CC} = 600 V, I_C = 40 A, V_{GE} = 15 V, R_g = 5 Ω, L = 200 µH, T_J = 25 °C, energy losses include tail and diode reverse recovery	-	0.76	-	mJ
Turn-off switching loss	E_{off}		-	1.14	-	
Total switching loss	E_{tot}		-	1.9	-	
Turn-on switching loss	E_{on}	V_{CC} = 600 V, I_C = 40 A, V_{GE} = 15 V, R_g = 5 Ω, L = 200 µH, T_J = 125 °C, energy losses include tail and diode reverse recovery	-	1.02	-	
Turn-off switching loss	E_{off}		-	1.83	-	
Total switching loss	E_{tot}		-	2.85	-	
Input capacitance	C_{ies}	V_{GE} = 0 V V_{CC} = 25 V f = 1.0 MHz	-	3200	-	pF
Output capacitance	C_{oes}		-	220	-	
Reverse transfer capacitance	C_{res}		-	80	-	
Reverse bias safe operating area	RBSOA	T_J = 150 °C, I_C = 120 A V_{CC} = 800 V, V_p = 1200 V R_g = 10 Ω, V_{GE} = + 15 V to 0 V		Fullsquare		
Short circuit safe operating area	SCSOA	T_J = 150 °C, V_{CC} = 600 V, V_p = 1200 V V_{GE} = + 15 V to 0 V	5	-	-	µs

DIODE SPECIFICATIONS (T_J = 25 °C unless otherwise specified)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Diode forward voltage drop	V_{FM}	I_C = 40 A	-	2.98	3.38	V
		I_C = 80 A	-	3.90	-	
		I_C = 40 A, T_J = 125 °C	-	3.08	-	
		I_C = 80 A, T_J = 125 °C	-	4.29	-	
		I_C = 40 A, T_J = 150 °C	-	3.12	-	
Reverse recovery energy of the diode	E_{rec}	V_{GE} = 15 V, R_g = 5 Ω, L = 200 µH V_{CC} = 600 V, I_C = 40 A T_J = 125 °C	-	574	-	µJ
Diode reverse recovery time	t_{rr}		-	120	-	ns
Peak reverse recovery current	I_{rr}		-	43	-	A

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Junction and storage temperature range		T_J, T_{Stg}		-40	-	150	°C
Junction to case	IGBT	R_{thJC}		-	-	0.41	°C/W
	Diode			-	-	0.61	
Case to sink per module		R_{thCS}		-	0.06	-	
Clearance [1]			External shortest distance in air between 2 terminals	5.5	-	-	mm
Creepage [2]			Shortest distance along external surface of the insulating material between 2 terminals	8	-	-	
Mounting torque to heatsink			A mounting compound is recommended and the torque should be checked after 3 hours to allow for the spread of the compound. Lubricated threads.	3 ± 10 %			Nm
Weight				66			g

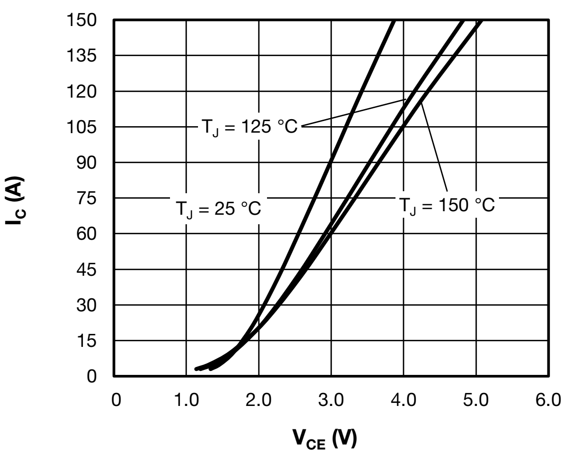


Fig. 1 - Typical Trench IGBT Output Characteristics, V_{GE} = 15 V

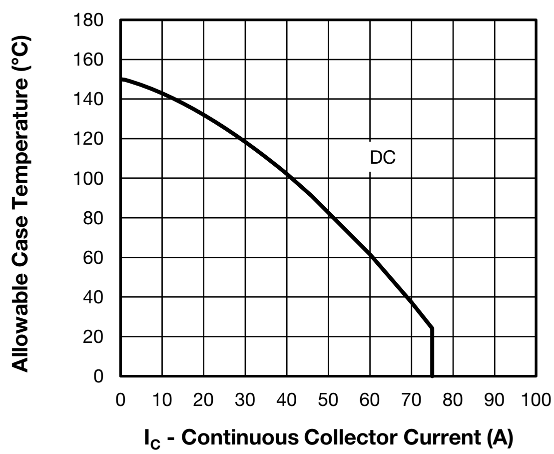


Fig. 3 - Maximum Trench IGBT Continuous Collector Current vs. Case Temperature

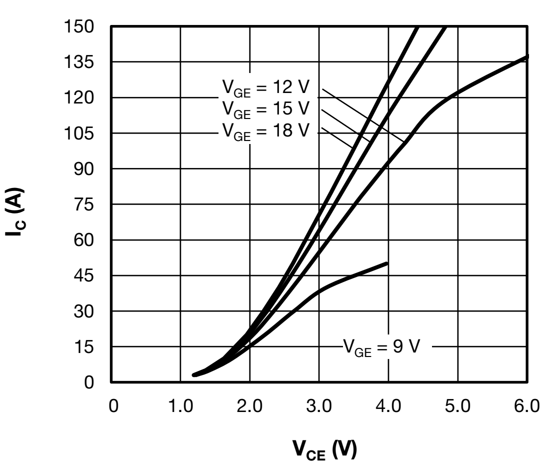


Fig. 2 - Typical Trench IGBT Output Characteristics, T_J = 125 °C

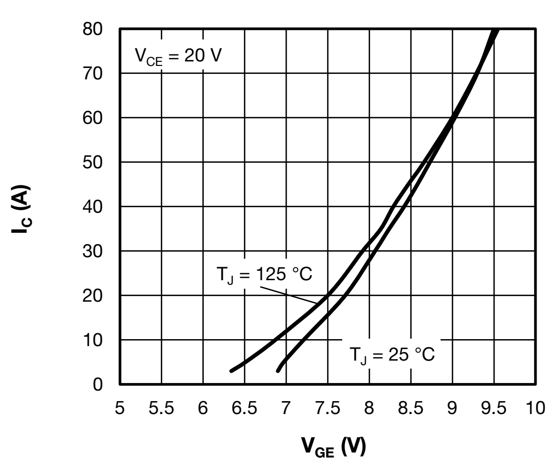


Fig. 4 - Typical Trench IGBT Transfer Characteristics

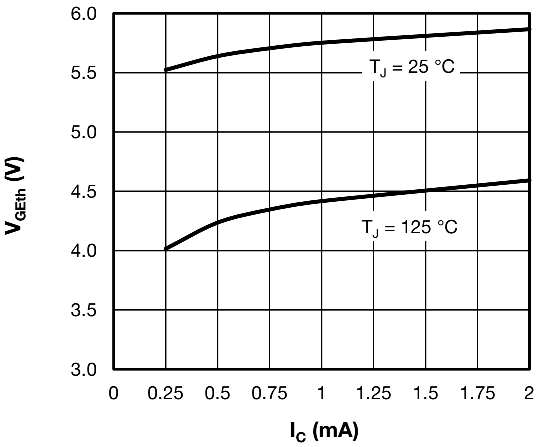


Fig. 5 - Typical Trench IGBT Gate Threshold Voltage

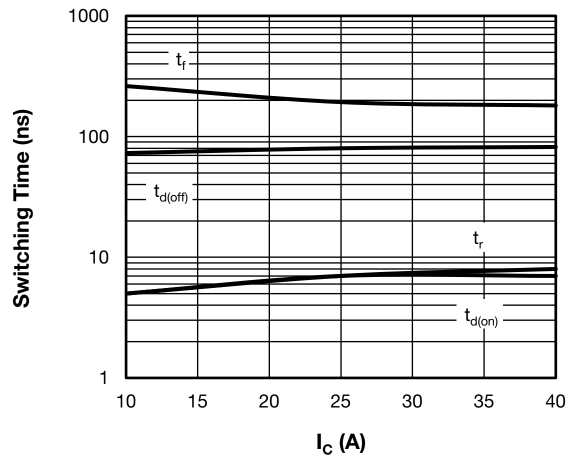


Fig. 8 - Typical Trench IGBT Switching Time vs. I_C (with Antiparallel Diode)
T_J = 125 °C, V_{CC} = 600 V, R_g = 4.7 Ω, V_{GE} = +15V/-15V, L = 500 μH

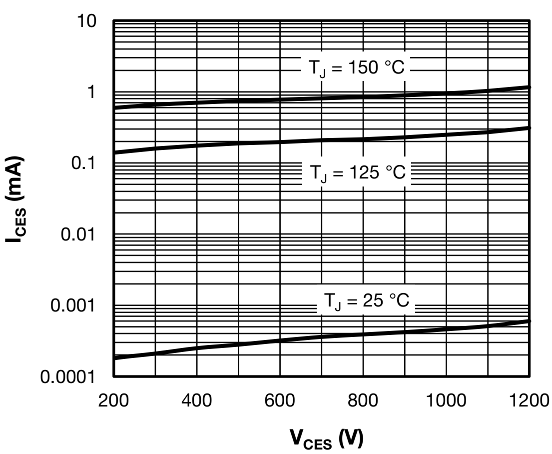


Fig. 6 - Typical Trench IGBT Zero Gate Voltage Collector Current

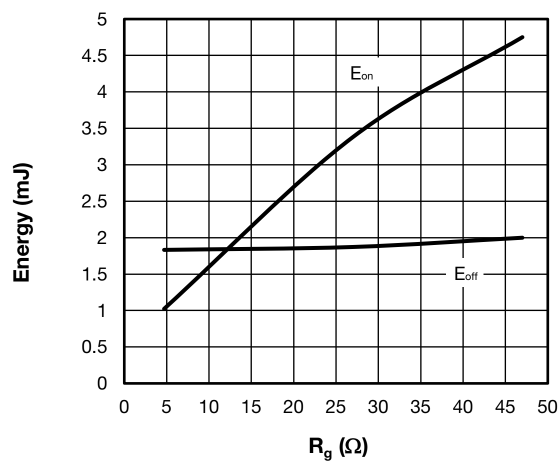


Fig. 9 - Typical Trench IGBT Energy Loss vs. R_g (with Antiparallel Diode)
T_J = 125 °C, V_{CC} = 600 V, I_C = 40 A, V_{GE} = +15V/-15V, L = 500 μH

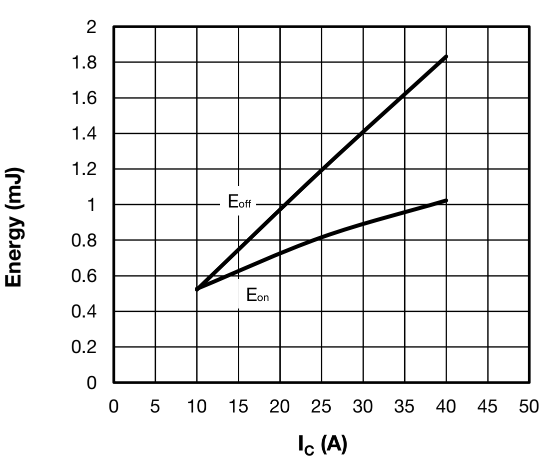


Fig. 7 - Typical Trench IGBT Energy Loss vs. I_C (with Antiparallel Diode)
T_J = 125 °C, V_{CC} = 600 V, R_g = 4.7 Ω, V_{GE} = +15V/-15V, L = 500 μH

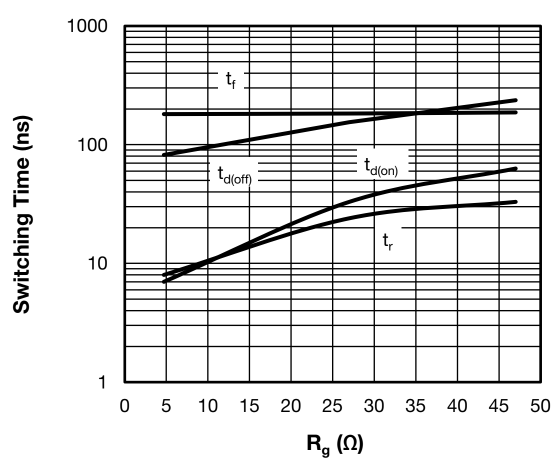


Fig. 10 - Typical Trench IGBT Switching Time vs. R_g (with Antiparallel Diode)
T_J = 125 °C, V_{CC} = 600 V, I_C = 40 A, V_{GE} = +15V/-15V, L = 500 μH

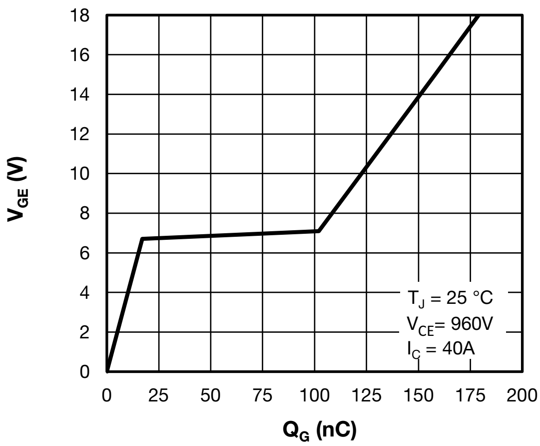


Fig. 11 - Typical Trench IGBT Gate Charge vs. Gate to Emitter Voltage

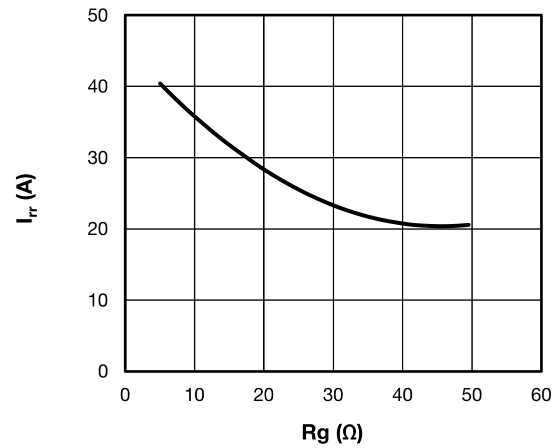


Fig. 14 - Typical Diode I_{rr} vs. R_g
T_J = 125 °C; I_F = 40 A

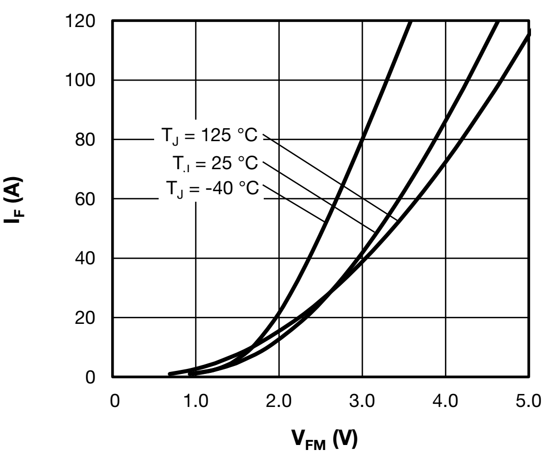


Fig. 12 - Typical Diode Forward Characteristics

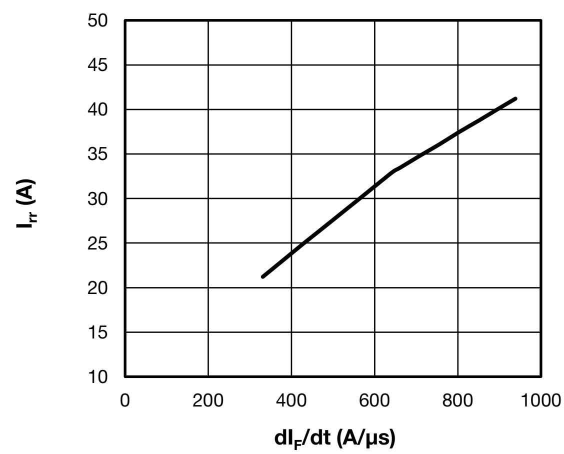


Fig. 15 - Typical Diode I_{rr} vs. dI_F/dt
V_{CC} = 600 V; V_{GE} = 15 V; I_{CE} = 40 A; T_J = 125 °C

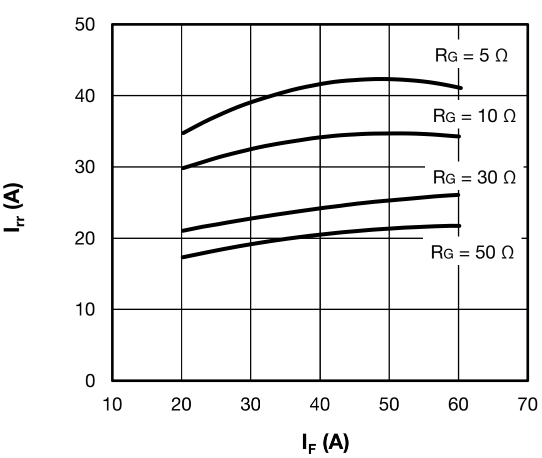


Fig. 13 - Typical Diode I_{rr} vs. I_F,
T_J = 125 °C

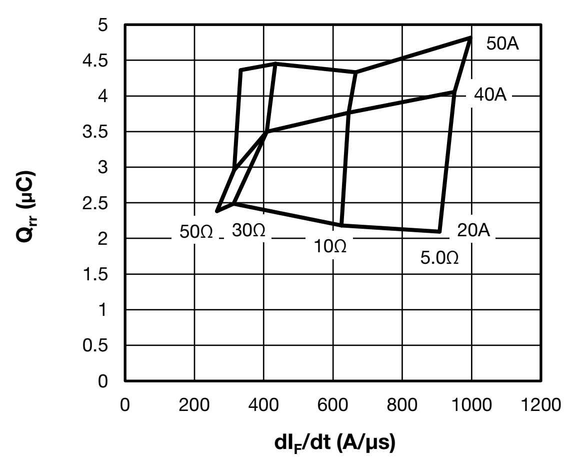


Fig. 16 - Typical Diode Q_{rr} vs. dI_F/dt
V_{CC} = 600 V; V_{GE} = 15 V; T_J = 125 °C

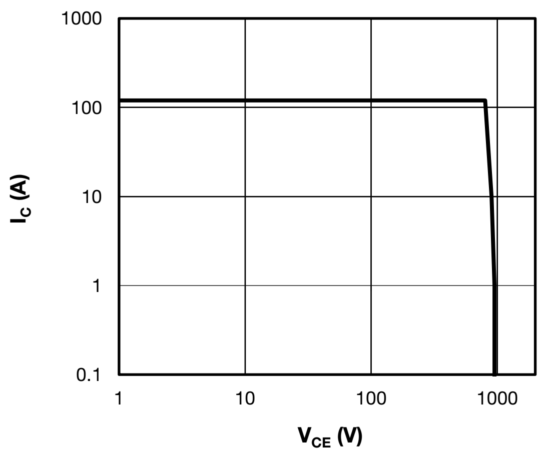


Fig. 17 - Trench IGBT Reverse BIAS SOA
T_J = 150 °C, I_C = 120 A, R_g = 10 Ω, V_{GE} = +15V / 0V, V_{CC} = 800 V, V_p = 1200 V

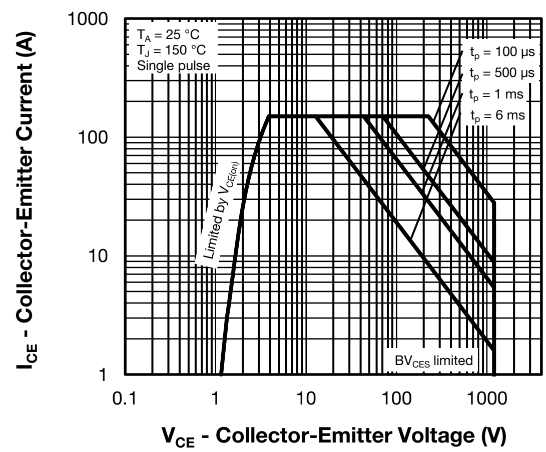


Fig. 18 - Trench IGBT Safe Operating Area

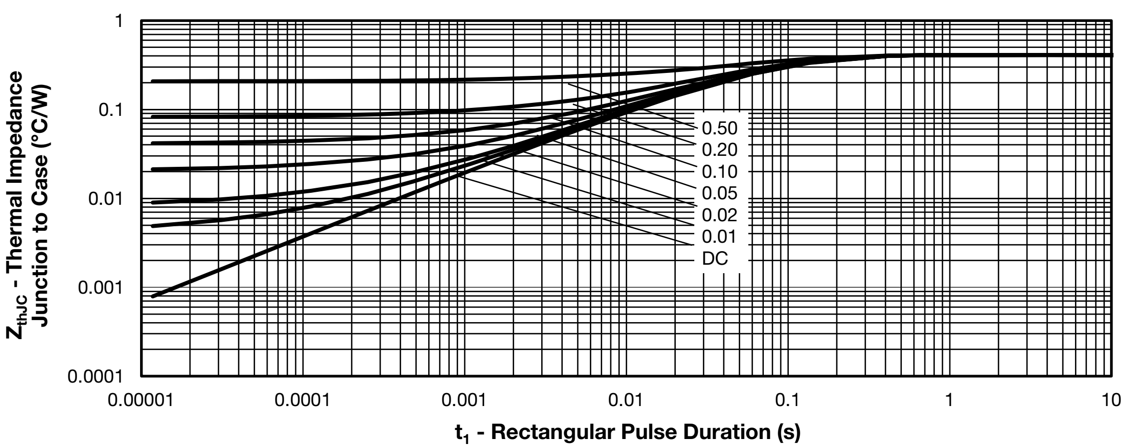


Fig. 19 - Maximum Trench IGBT Thermal Impedance Z_{thJC} Characteristics

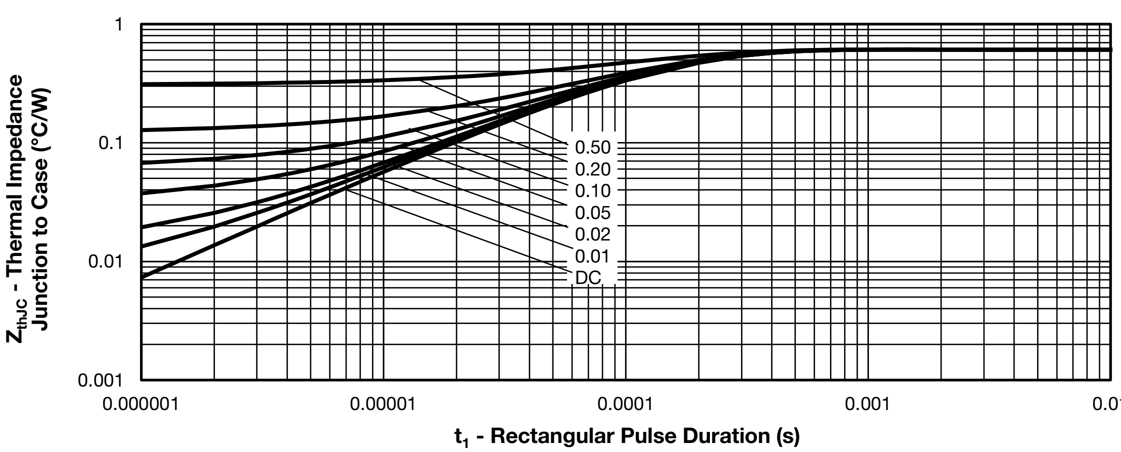


Fig. 20 - Maximum Diode Thermal Impedance Z_{thJC} Characteristics

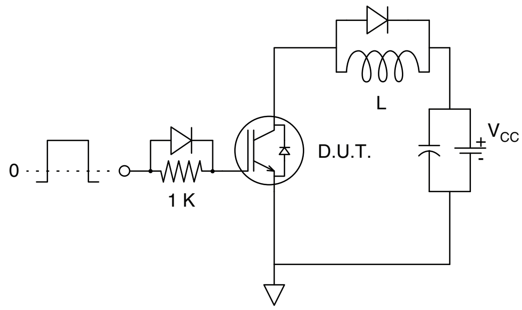


Fig. 21 - Gate Charge Circuit (Turn-Off)

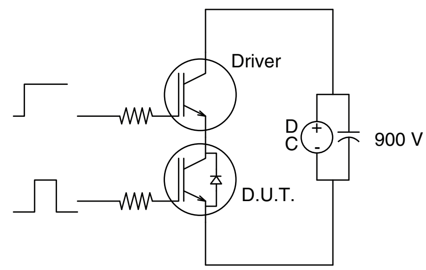


Fig. 23 - S.C. SOA Circuit

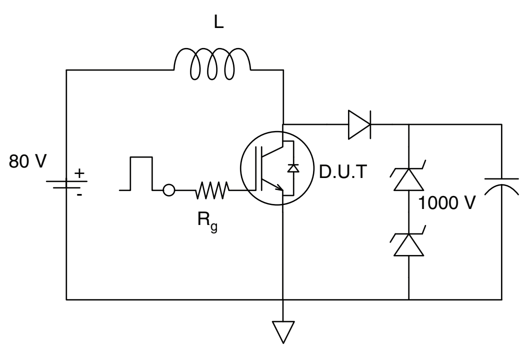


Fig. 22 - RBSOA Circuit

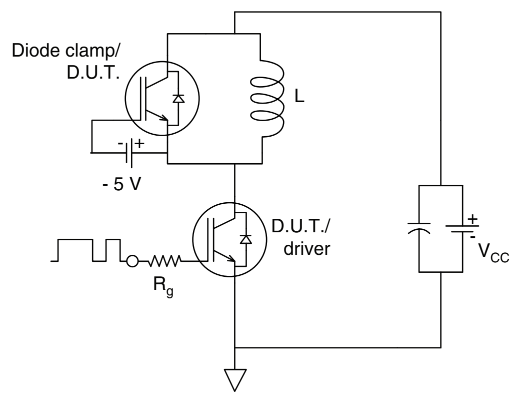


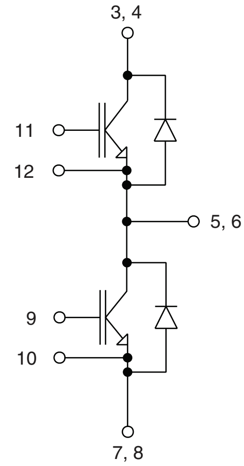
Fig. 24 - Switching Loss Circuit

ORDERING INFORMATION TABLE

Device code	VS-	40	MT	120	P	H	A	PbF
	1	2	3	4	5	6	7	8

1	-	Vishay Semiconductors product
2	-	Current rating (40 = 40 A)
3	-	Essential part number
4	-	Voltage code (120 = 1200 V)
5	-	Speed / type (P = trench IGBT)
6	-	Circuit configuration (H = half bridge)
7	-	A = Al_2O_3 DBC substrate
8	-	PbF = lead (Pb)-free

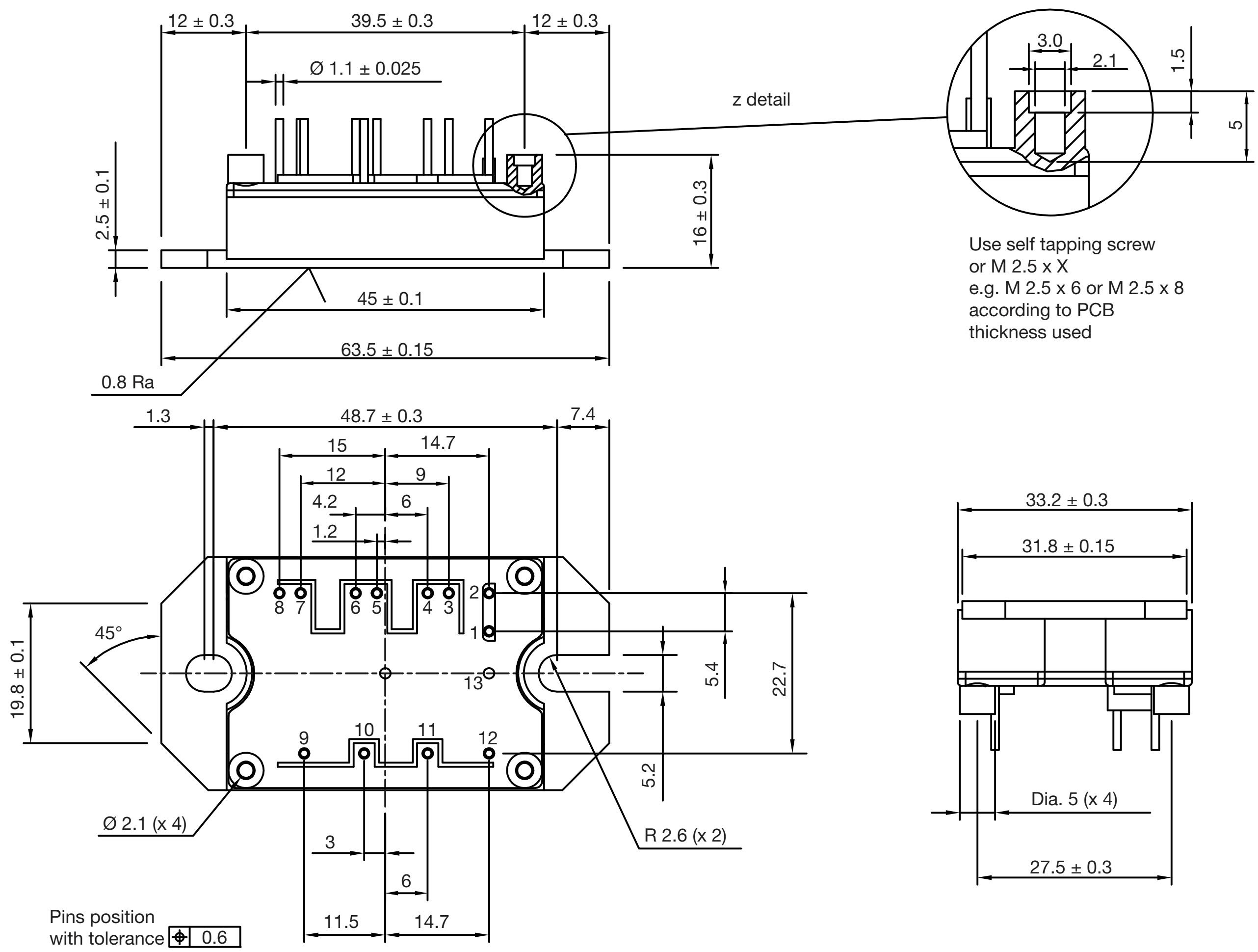
CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95175

MTP

DIMENSIONS in millimeters



Note

- Unused terminals are not assembled in the package

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